

2N6605
2N6606
2N6607
2N6608

**SILICON CONTROLLED RECTIFIER
0.35 AMP, 30 THRU 200 VOLTS**



TO-18 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6605 Series types are hermetically sealed silicon controlled rectifiers manufactured in a TO-18 case, designed for control systems and sensing circuit applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_C=25°C)

	SYMBOL	<u>2N6605</u>	<u>2N6606</u>	<u>2N6607</u>	<u>2N6608</u>	UNITS
Peak Repetitive Off-State Voltage	V _{DRM} , V _{RRM}	30	60	100	200	V
Average On-State Current	I _O		0.35			A
Peak One Cycle Surge Current (t=8.3ms)	I _{TSM}		6.0			A
Peak Gate Voltage	V _{GM}		8.0			V
Operating Junction Temperature	T _J		-40 to +125			°C
Storage Temperature	T _{stg}		-40 to +150			°C

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

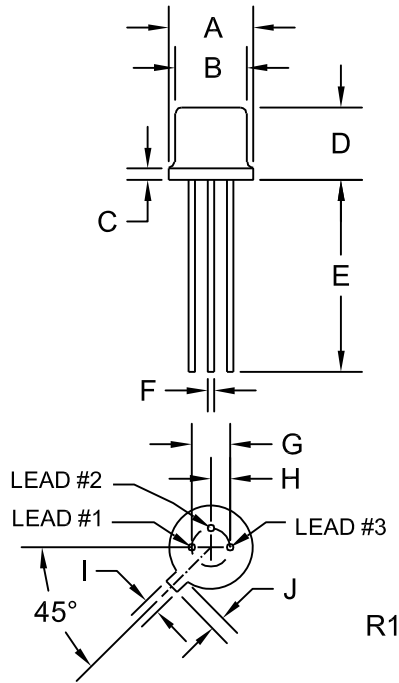
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{DRM}	Rated V _{DRM} , R _{GK} =1.0KΩ		120	nA
I _{RDM}	Rated V _{RRM}		250	nA
I _{GT}	V _D =6.0V, R _L =100Ω		200	μA
V _{GT}	V _D =6.0V, R _L =100Ω		0.8	V
V _{TM}	I _T =2.0A		2.0	V
I _H	R _{GK} =1.0KΩ		5.0	mA

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TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Cathode
- 2) Gate
- 3) Anode

MARKING: FULL PART NUMBER

R0 (30-March 2011)